

## CLAIMS

1. A semiconductor light emitting device, comprising:

a semiconductor multilayer structure composed of a  
5 p-semiconductor layer, a quantum well emission layer, and an  
n-semiconductor layer each made of a nitride semiconductor and  
laminated in the stated order, light from the emission layer  
exitting through the n-semiconductor layer; and

10 a p-electrode facing and in ohmic contact with the  
p-semiconductor layer, wherein

the p-semiconductor layer has an intensive-injection  
region into which an electric current from the p-electrode is  
injected more intensively than another region, the  
intensive-injection region spanning substantially across an  
15 entire surface of the p-semiconductor layer.

2. The semiconductor light emitting device according to Claim  
1, wherein

the intensive-injection region is realized by a contact  
20 structure of the p-electrode with the p-semiconductor layer.

3. The semiconductor light emitting device according to Claim  
2, wherein

the p-electrode has, on a surface facing toward the  
25 p-semiconductor layer, a plurality of projections or depressions  
that are distributed substantially uniformly, and

the p-electrode is in contact with the p-semiconductor layer  
at a top surface thereof.

4. The semiconductor light emitting device according to Claim 3, wherein

the p-electrode is made of a metal that reflects light from  
5 the emission layer toward the n-semiconductor layer.

5. The semiconductor light emitting device according to Claim 4, further comprising

an insulator disposed on a recessed surface of the  
10 p-electrode to fill a space between the recessed surface and  
the p-semiconductor layer.

6. The semiconductor light emitting device according to Claim 5, wherein

15 the insulator is made of a material transparent to light emitted by the emission layer.

7. The semiconductor light emitting device according to Claim 5, wherein

20 the insulator has a substantially same refractive index as a refractive index of the nitride semiconductor forming the p-semiconductor layer.

8. The semiconductor light emitting device according to Claim 3, wherein

a drive current for driving the semiconductor light emitting device is maintained within such a range that results in an average current density not exceeding 50 A/cm<sup>2</sup>, the average current

density being calculated by dividing the drive current by an area of a main surface of the emission layer,

the p-electrode faces substantially entirely of the main surface of the emission layer, and

5 a ratio between the top and recessed surfaces of the p-electrode is determined so that an electric current flowing through the top surface of the p-electrode measures at least 100 A/cm<sup>2</sup> in current density.

10 9. The semiconductor light emitting device according to Claim 3, wherein

the p-semiconductor layer has, on a surface facing toward the p-electrode, a high-defect region in which lattice defects are localized and a low-defect region formed adjacent to the 15 high-defect region, and

the p-electrode is in contact with the low-defect region of the p-semiconductor layer.

10. The semiconductor light emitting device according to Claim 20 1, wherein

the intensive-injection region is realized by a contact structure of the p-semiconductor layer with the p-electrode.

11. The semiconductor light emitting device according to Claim 25 10, wherein

the semiconductor multilayer structure has, on a surface facing toward the p-electrode, a plurality of projections or depressions that are distributed substantially uniformly, and

the semiconductor multilayer structure is in contact with the p-electrode at a top surface of the p-semiconductor layer.

12. The semiconductor light emitting device according to Claim 5 11, wherein

the p-electrode is made of a metal that reflects light from the emission layer toward the n-semiconductor layer.

13. The semiconductor light emitting device according to Claim 10 11, wherein

a recessed surface of the semiconductor multilayer structure is present in the n-semiconductor layer.

14. The semiconductor light emitting device according to Claim 15 11, wherein

the semiconductor multilayer structure has, on the surface facing toward the p-electrode, a high-defect region in which lattice defects are localized and a low-defect region formed adjacent to the high-defect region, and

20 the low-defect region is present at the top surface of the semiconductor multilayer structure.

15. The semiconductor light emitting device according to Claim 1, further comprising:

25 a base substrate supporting the semiconductor multilayer structure from a direction of the p-semiconductor layer; and

a phosphor film disposed on a main surface of the semiconductor multilayer structure facing away from the base

substrate, the phosphor film extending across a side surface of the semiconductor multilayer structure to the base substrate.

16. A lighting module comprising:

5           a mounting substrate; and  
             the semiconductor light emitting device as defined in any one of Claims 1-15.

17. A lighting device comprising, as a light source, the lighting

10         module as defined in Claim 16.

18. A surface mounting device comprising:

15         a substrate;  
             a semiconductor light emitting device as defined in any one of Claims 1-15, and mounted on the substrate; and  
             a resin molding the semiconductor device.

19. A dot-matrix display device comprising:

20         semiconductor light emitting devices as defined in any one of Claims 1-15 and are arranged in a matrix.